



**PATENT** 

Attorney Docket No.: SAM-0234

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.:

Applicant(s): Sung-bae Park, et al.

09/924,787

Examiner: Lewis, M. Group Art Unit: 2822

Filed: Title:

August 8, 2001

SOI MOSFET HAVING BODY CONTACT FOR PREVENTING FLOATING

BODY EFFECT AND METHOD OF FABRICATING THE SAME

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

I hereby certify that this correspondence is being deposited with the United States Post Office as First Class Mail on the date indicated below in an envelope addressed to BOX NON-FEE AMENDMENT, Assistant Commissioner, 67-Patents, Washington, DC 20231.

Lisa Sanders

**BOX NON-FEE AMENDMENT** 

Assistant Commissioner for Patents

Washington, D.C. 20231

## **AMENDMENT A**

Sir:

This is in response to the Office Action mailed on May 22, 2002.

Please amend the application as follows:

## In the Claims

Please amend the claims as follows:

(Amended) A silicon-on-insulator metal oxide semiconductor field effect transistor (SOI 1.

MOSFET) comprising:

- a semiconductor substrate;
- a buried oxide layer formed on the semiconductor substrate;
- a body on the buried oxide layer, the body being an active region of a transistor;
- a gate oxide layer formed, on the body;
- a gate formed on the gate oxide layer;

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